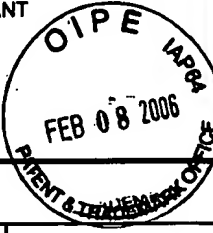


Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1531		SERIAL NO. 09/755,673	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Leonard F rbes, et al.			
				FILING DATE January 5, 2001		GROUP 2823	
U.S. PATENT DOCUMENTS							
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
KN	AA	6,203,613 B1	03/01	Gates, et al.	117	104	10/19/1999
↓	AB	6,509,280 B2	01/03	Choi, Sung-Je	438	778	02/13/2000
	AC	6,551,399 B1	04/03	Sneh, et al.	117	102	01/10/2000
	AD	6,576,053 B1	06/03	Kim, et al.	117	89	10/06/2000
	AE	6,580,111 B2	06/03	Kim, et al.	257	301	05/23/2001
	AF	6,664,186 B1	12/03	Callegari, et al.	438	681	09/29/2000
KN	AG	6,780,704 B1	08/04	Raaijmakers, et al.	438	239	12/03/1999
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	AN						
	AO						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AP						
	AQ						
EXAMINER		DATE CONSIDERED					
/Khien Nguyen/		06/20/2006					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>							

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT-AND-TRADEMARK-OFFICE

ATTY. DOCKET NO.
M122-1531

SERIAL NO.
Filed Herewith

LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT
Micron Technology, Inc.

FILING DATE
Filed Herewith

1/5/01

GROUP

2823

PTO
09/15/81
09/15/81
01/05/01

U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
AA						

FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation
					Yes No
AB					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

K.N.	AC	Abstract of: Oxidation of Sintered Aluminum Nitride at Near-ambient temperatures; Dutta, I.; Mitra, S.; Rabenberg, L.; Journal of the American Ceramic Society, Vol. 75, No. 11, pp. 3149-53, Nov. 1992
	AD	Abstract of: Oxidation of lead films by rf sputter etching in an oxygen plasma; J.H. Greiner
	AE	Abstract of: Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma; J.H. Greiner; Journal of Applied Physics; Vol. 42; Number 12; November 1971
	AF	Abstract of: Measurement of Tunnel Current Density in a Metal Oxide Metal System as a Function of Oxide Thickness; J.M. Eldridge and J. Maitsoo
	AG	Abstract of: Optical Measurement of Film Growth on Silicon and Germanium Surfaces in Room Air; R.J. Archer
	AH	Preparation of Al-O-N Films by Electron Cyclotron Resonance Plasma-Assisted Chemical Vapor Deposition; Takashi Goto; Wei Zhang; Toshio Hirai, 1999 Publication Board, Japanese Journal of Applied Physics; Vol. 38 (1999) Pt. 1, No. 6A; pp. 3668-74
✓	AI	Ion assisted deposition of oxynitrides of aluminum and silicon; G.A. Al-Jumaily and T.A. Mooney; W.A. Spurgeon and H.M. Dauplaise
K.N.	AJ	Abstract of: Preparation of aluminum nitride and oxynitride thin films by ion-assisted deposition; Targove, J.D.; Lingg, L.J.; Lehan, J.P. et al.; Conference: Materials Modification and Growth Using Ion Beams Symposium, pp. 311-16; Mater. Res. Soc., Pittsburgh, PA 1987

EXAMINER

Khuemnguyen

DATE CONSIDERED

08/16/02

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EL 465852887

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT-AND-TRADEMARK-OFFICE		ATTY. DOCKET NO. M122-1531		SERIAL NO. Filed Herein	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		09/755673	
				FILING DATE Filed Herein 1/5/01		GROUP 2823	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
AB							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC		Film Synthesis and Growth Using Energetic Beams; Material Research Society Symposium Proceedings Vol. 388; April 17-20, 1995 San Francisco, CA				
	AD		Some Properties of Chemically Vapor Deposited Films of Al_2O_3 on Silicon; E.A. Irene, V.J. Silvestri and G.R. Woolhouse; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 409-427				
	AE		Chemical Vapor Deposition of Al_2O_3 Films; V.J. Silvestri, E.A. Irene, S. Zirinsky, J.D. Kaptis; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 429-444				
	AF		Disk hydrogen plasma assisted chemical vapor deposition of aluminum nitride; T.Y. Sheng, Z.Q. Yu, and G.J. Collias; Appl. Phys. Lett. 52(7), February 1988; pp. 576-578				
	AG		Epitaxial Growth of Aluminum Nitride on Sapphire and Silicon; K. Dovidenko; S. Okuyabirsky; J. Narayan; and M. Razeghi; Mat. Res. Soc. Symp. Proc. Vol. 358; 1995 Materials Research Society; pp. 1023-1028				
	AH		III-Nitride, SiC and Diamond Materials for Electronic Devices; Materials Research Society, Symposium Proceedings Vol. 423; April 8-12, 1996, San Francisco, CA; pp. 667-672				
V	AI		Electrochemical Behaviour of AlN Films Prepared by Reactive Cathodic Sputtering; F. Vacandio, Y. Massiani, P. Grovier, L. Fedrizzi and D. Bida; Materials Science Forum; Vols. 289-292 (1998) pp. 689-697; 1998 Trans Tech Publications, Switzerland				
K.N.	AJ		Measurements of stress distribution in Si_3N_4 using AlN thin films; M. Akhama, C.N. Xu, K. Nonaka, T. Watanabe; Journal of Materials Science Letters (1998) pp. 2093-2095				
EXAMINER				DATE CONSIDERED			
Khemnguyen				08/16/02			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1531		SERIAL NO. Filed-Herein	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micrus Technology, Inc.		09/755673	
				FILING DATE Filed-Herein		GROUP 2823	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA						
	AB						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AC						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AD		Changes in optical transmittance and surface morphology of AlN thin films exposed to atmosphere; Yoshihisa Watanabe, Yoshifumi Sakuragi, Yoshiki Amamoto, and Yoshikazu Nakamura; J. Mater. Res., Vol 13, No. 10, Oct. 1998; 1998 Materials Research Society; pp. 2956-61				
	AE		Optical Interference Coatings; Florin Abeles, Chair/Editor; Proceedings Europto Series; SPIE Vol. 2253; part 2 of 2; pp. 1275-85				
	AF		Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics; Ying Shi; Xiewen Wang; T.P. Ma; IEEE Electron Device Letters, Vol. 19, No. 10, October 1998; pp. 388-390				
	AG		High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for Deep Sub-micron CMOS Technology; Xin Guo, Xiewen Wang; Sijiang Luo, T.P. Ma, and T. Tamagawa; Dept. of Electrical Engineering, Yale University, New Haven, CT 06520				
	AH		High Quality Ta ₂ O ₅ Gate Dielectrics with T _{ox} < 10Å; H. F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.L. Mao, Y. Senzaki, D. Roberts and D.L. Kwong				
↓	AI		Abstract of: Low interface trap density for remote plasma deposited SiO ₂ /sub 2/ on n-type GaN; Applied Physics Letters, Vol. 68, No. 13; pp. 1850-2				
K.N.	AJ		Abstract of: Interface-state characteristics of GaN/GaAs MIS capacitors; Solid-State Electronics, vol. 25, no. 8, pp. 811-15				
EXAMINER K. Bremminger				DATE CONSIDERED 08/16/02			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1531		SERIAL NO. <u>Filed Herein</u>	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		09/755673	
				FILING DATE Filed Herein 1/5/01		GROUP 2823	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AB							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC	Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-on-Insulator Materials; Stefan Bengtsson, Mats Bergh, Manolis Choumas, Christian Olesen and Kjell O. Jeppson; Jpn. J. Appl. Phys. Vol. 35 (1996) Pt. 1, No. 8; pp. 4175-81					
	AD	Characteristics of AlN Thin Films Deposited by Electron Cyclotron Resonance Dual-Ion-Beam Sputtering and their Application to GHz-Band Surface Acoustic Wave Devices; Hiroshi Okano, Naoki Tanaka, Yasuhiro Hirao, Yasumi Kobayashi, Kenichi Shibata and Shoichi Nakano; Jpn. J. Appl. Phys. Vol. 33 (1994); Pt. 1, No. 5B; pp. 2957-2961					
	AE	An Aluminum Oxynitride Film; Wang Dehuang, Guo Liang; Thin Solid Films, 198 (1991) pp. 207-210					
	AF	Formation of aluminum oxynitride diffusion barriers for Ag metallization; Y. Wang and T. L. Afford; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; American Institute of Physics; pp. 52-54					
	AG	Abstract of: Simulation of Hyperthermal deposition of Si and C on SiC surfaces; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; 1999 American Institute of Physics					
↓	AH	Nitrogen plasma source ion implantation for corrosion protection of aluminum 6061-T4; J. H. Booske, L. Zhang, W. Wang, K. Menze, N. Zjaba, C. Baum, and J.L. Shober; J. Mater. Res. Vol. 12, No. 5, May 1997; 1997 Materials Research Society; pp. 1356-66					
	AI	Thickness measurement of submonolayer native oxide films on silicon wafers; Fuhe Li, Marjorie K. Balazs, Bruce E. Deal; Wafers & Substrates; Solid State Technology, February 2000; pp. 87, 88, 92, 94, 96, 98					
K.N.	AJ	Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon; James Kolodzey et al.; IEEE Transactions on Electron Devices; Vol. 47, No. 1, January 2000; pp. 121-128					
EXAMINER <i>Khemnguyen</i>				DATE CONSIDERED 08/16/02			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form-PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1531		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		09/755 673	
						FILING DATE Filed Herewith 1/5/01	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA							
FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AB							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC	Structural, Optical and Electronic Properties of Oxidized AlN Thin Films at Different Temperatures; Enam Ahmed Chowdhury et al.;					
↓	AD	Formation of Al-nitride films at room temperature by nitrogen ion implantation into aluminum; N. Lieske and R. Hezel; J. Appl. Phys. 52(9), Sept. 1981; pp. 5806-5810					
↓	AE						
↓	AF						
↓	AG						
↓	AH						
↓	AI						
K.N.	AJ						
EXAMINER K. N. Nguyen				DATE CONSIDERED 08/16/02			
<small>*EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							